IN THE SPECIFICATION:

Please amend the specification as follows:

Please amend the paragraph bridging pages 12 and 13, from line 16 on page 12 through line 8 on page 13, as follows:

That is, a film of tunneling magnetoresistive film 50 is firstly formed, which comprises a lower gap layer 13 composed of Mo, for example, a seed layer 15 composed of a metal for controlling the orientation of stacked films formed thereon, for example, 81 at.% Ni –19 at.% Fe, an antiferromagnetic layer 16 composed of 52 at.% Pt -48 at.% Mn, a second ferromagnetic layer 17 composed of 75 at.% Co -25 at.% Fe, a tunneling barrier 18 composed of aluminum oxide, and a first ferromagnetic layer 19 composed of 81 at.% Ni –19 at.% Fe. Subsequently, a longitudinal biasing layer 201 is laminated thereon, which comprises an underlayer for a longitudinal biasing layer 22 composed of, for example, Cu, Ta, Ru, or stacked films thereof, a soft magnetic layer <u>23</u> for longitudinal biasing composed of, for example, Ni-Fe alloy, Co-Fe alloy, Fe or stacked films thereof, and a pinning layer <u>24</u> for longitudinal biasing [[24]] composed of, for example, Mn-Ir system antiferromagnetic layer or Co-Cr-Pt system hard magnetic layer. Then, an upper gap layer 14 is further laminated thereon.

Please amend the paragraph on page 19, from lines 1 through 7, as follows:

Further, with the first lead line 31 thus formed, a stress is acted on the lower shield layer. Even if a magnetic domain originates due to the stress, a magnetic domain wall is pinned on the boundary between the lower shield layer 111 and the lead contact portion <u>113</u> attached to the lower shield layer <u>111</u> [[113]], a noise is not generated during a reproducing operation.

Please amend the paragraphs on pages 20 and 21, from line 17 on page 20 through line 16 on page 21, as follows:

In the above Examples 1 to 3, there are described structures where a lead contact portion attached to the shield layer and connected to a lead line is provided on the edge parallel to the track width direction of the shield layer. The Example 4 shows a structure where the lead contact portion attached to the <u>shield</u> ~~shied~~ layer is provided on the edge perpendicular to the track width direction of the shield layer. Fig. 13 is an overhead view and a partial overhead view when the upper shield layer 12 is cut off. Fig. 14 is a diagram in

which the lower shield layer 111, the first lead line 31, the upper shield layer 12 and the second lead line 32 are projected onto the plane on which the lower shield layer 111 is disposed.

On the both edges perpendicular to the track width direction of the lower shield layer 111, a lead contact portion 113 is disposed having a height shorter than the height in the stripe height direction of the lower shield layer 111. At the lead contact portion 113, the first lead line 31 is electrically connected with the lower shield layer 111. Further, on the both edges perpendicular to the track width direction of the upper shield layer 12, a lead contact portion 123 is disposed having a height shorter than the height in the stripe height direction of the upper shield layer 12, and at the lead contact portion 123, the second lead line 32 is electrically connected with the upper shield layer 12.

Please amend the paragraphs on page 23, from lines 7 through 23, as follows:

In the Example 4, the lead contact portion 123 attached to the upper shield layer 12 [[123]] overlaps the first lead line 31 and the lead contact portion 113 attached to the lower shield layer 111 [[113]], thereby forming capacitance C. Fig. 15 and Fig. 16 show structures with which the capacitance C thus generated can be reduced.

In this structure, the lead contact portion 113 attached to the lower shield layer 111 [[113]] and the lead contact portion 123 attached to the upper shield layer 12 [[123]] are arranged on the edges perpendicular to the track width direction of the shield layer in such a manner as not overlapped by each other. With this arrangement, the upper shield layer 12 and its lead contact portion 123 does not overlap the first lead line 31, and further, the second lead line 32 does not overlap the lower shield layer 111 and its lead contact portion 113. Therefore, it is possible to reduce the capacitance C.

Please amend the paragraphs on pages 28 and 29, from line 1 on page 28 through line 2 on page 29, as follows:

As described above in detail, according to the present invention, in the magnetoresistive head of CPP structure to which a CPP type magnetoresistive layer is applied, which has a tunneling magnetoresistive effect or CPP-GMR effect, the first lead line 31 is electrically connected to a lead contact portion 113 attached to a lower shield layer 111 [[113]], within a same plane, the width of the lead contact portion 113 either being equal to or shorter than a maximum length in the track width direction of the lower shield layer 111. Alternatively, the first lead line 31 is electrically connected to a lead contact portion 113

attached to a lower shield layer 111 [[113]], the height thereof either being equal to or shorter than the maximum length in the stripe height direction of the lower shield layer 111. With the structures above, it is possible to prevent that a bump is generated on the upper shield layer 12 by the first lead line 31, and that a magnetic domain is formed by the bump, which is a cause of noise generation. Therefore, it is possible to supply a magnetic head with less noise.

Further, similar to the case of the first lead line 31, the second lead line 32 may also be structured so that it is electrically connected at the lead contact portion 123 attached to the upper shield layer 12 [[123]] provided in the upper shield layer 12, whereby it is possible to not only reduce capacitance C, but also reduce noise ~~not only reducing noises~~. Therefore, it is possible to supply a magnetic head with a high yield, superior in high frequency performance.